

**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Design for inverter supply application

品名 : FH4240TN**	
<b>I<sub>T(AV)</sub></b>	<b>4240A</b>
<b>V<sub>DRM</sub></b>	<b>1200V~2000V</b>
<b>V<sub>R RM</sub></b>	<b>1000V~1800V</b>
<b>t<sub>q</sub></b>	<b>15~80μs</b>

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T <sub>J</sub> (°C)	VALUE			UNIT
					Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T <sub>C</sub> =55°C	125			4240	A
V <sub>DRM</sub>	Repetitive peak off-state voltage	tp=10ms		125	1200		2000	V
V <sub>R RM</sub>	Repetitive peak reverse voltage				1000		1800	V
I <sub>DRM</sub> I <sub>R RM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>R RM</sub>		125			250	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave		125			46	kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination	V <sub>R</sub> =0.6V <sub>R RM</sub>						10580
V <sub>TO</sub>	Threshold voltage			125			1.14	V
r <sub>T</sub>	On-state slope resistance						0.10	mΩ
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =5000A, F=70kN	15μs≤t <sub>q</sub> ≤35μs	25			2.50	V
			36μs≤t <sub>q</sub> ≤60μs				1.80	V
			61μs≤t <sub>q</sub> ≤80μs				1.60	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>		125			1000	V/μs
di/dt	Critical rate of rise of on-state current (Non-repetitive)	V <sub>DM</sub> = 67%V <sub>DRM</sub> ,to4000A Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A		125			1200	A/μs
Q <sub>tr</sub>	Recovery charge	I <sub>TM</sub> =2000A, tp=4000μs, di/dt=-20A/μs, V <sub>R</sub> =100V		125		2100		μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =2000A, tp=4000μs, V <sub>R</sub> =100V dv/dt=30V/μs ,di/dt=-20A/μs		125	15		80	μs
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A		25	40		450	mA
V <sub>GT</sub>	Gate trigger voltage				0.9		4.5	V
I <sub>H</sub>	Holding current				20		1000	mA
I <sub>L</sub>	Latching current						1000	mA
V <sub>GD</sub>	Non-trigger gate voltage				V <sub>DM</sub> =67%V <sub>DRM</sub>		125	
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	D.C. double side cooled Clamping force 70 kN					0.007	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink						0.002	
F <sub>m</sub>	Mounting force				63		84	kN
T <sub>vj</sub>	Junction temperature				-40		125	°C
T <sub>stg</sub>	Stored temperature				-40		140	°C
W <sub>t</sub>	Weight					1390		g
Outline	P20							

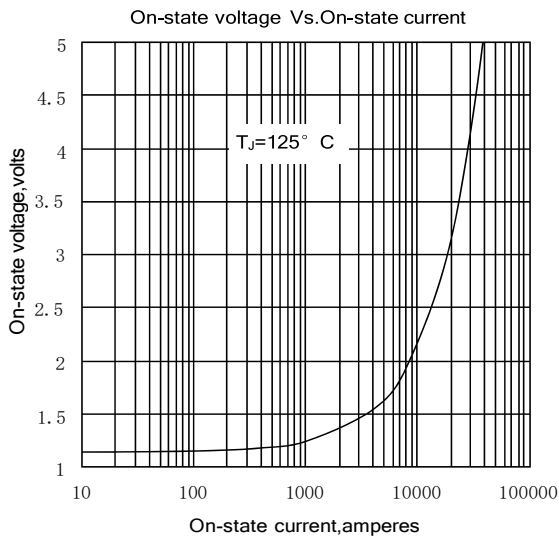


Fig.1

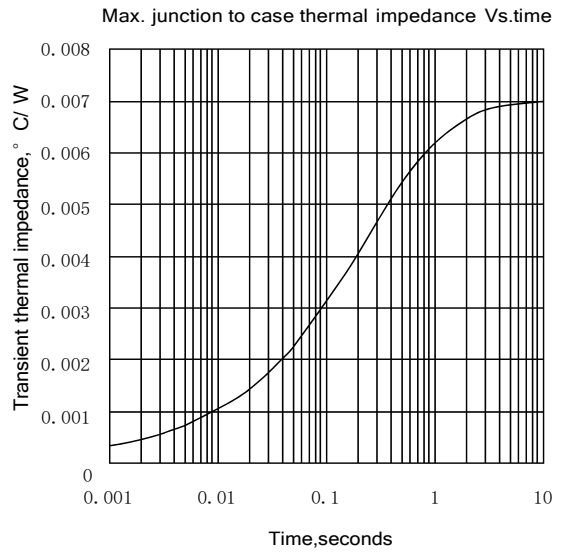


Fig.2

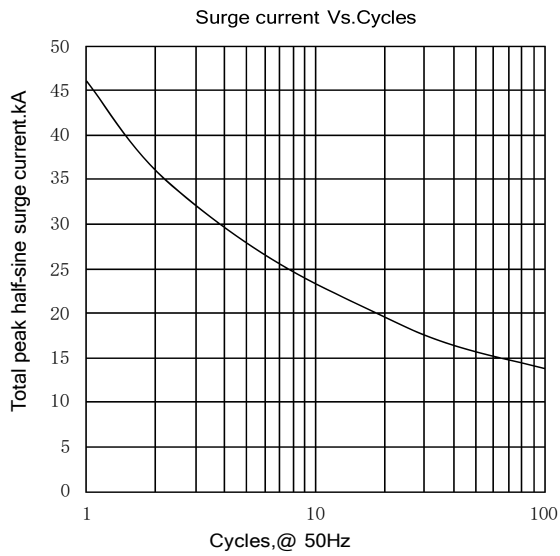


Fig.3

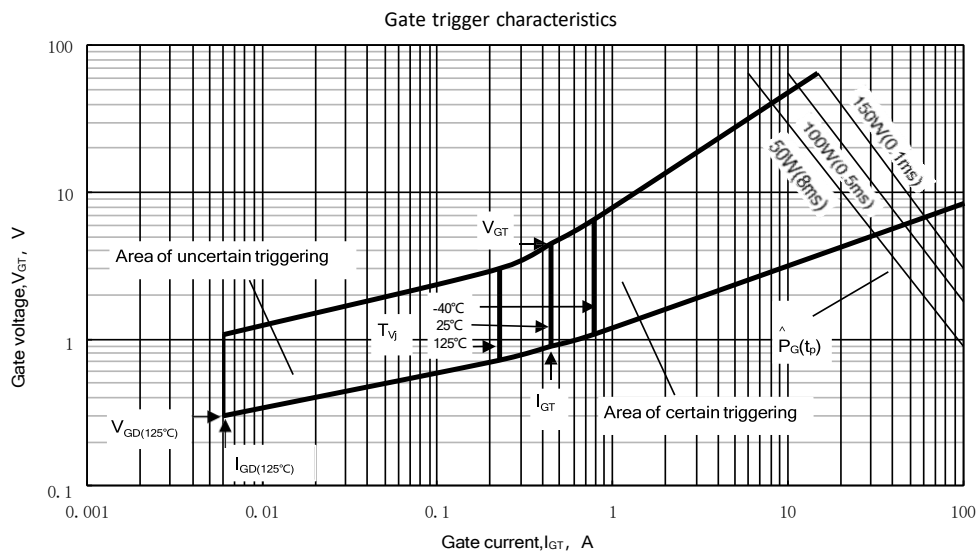
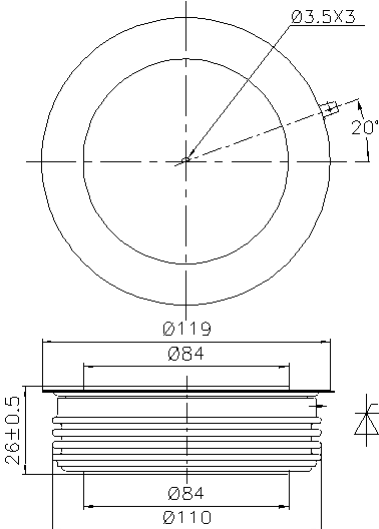


Fig.4

**Outline:**



Nlps reserves the right to change specifications without notice.